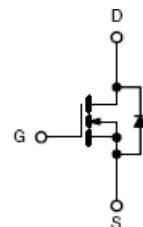


# SOT-23 Plastic-Encapsulate MOSFETS

## BC2302 N-Channel 20-V(D-S) MOSFET

### FEATURE

TrenchFET Power MOSFET



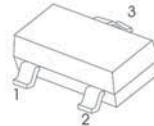
### APPLICATIONS

- Load Switch for Portable Devices

DC/DC Converter

### Equivalent Circuit

### SOT-23



1. GATE
2. SOURCE
3. DRAIN

MARKING CODE: "2302" OR "S2"

### Maximum ratings ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current	$I_D$	2.1	A
Continuous Source-Drain Current(Diode Conduction)	$I_S$	0.6	
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient ( $t \leq 5\text{s}$ )	$R_{\theta JA}$	357	°C/W
Operating Junction	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 ~ +150	

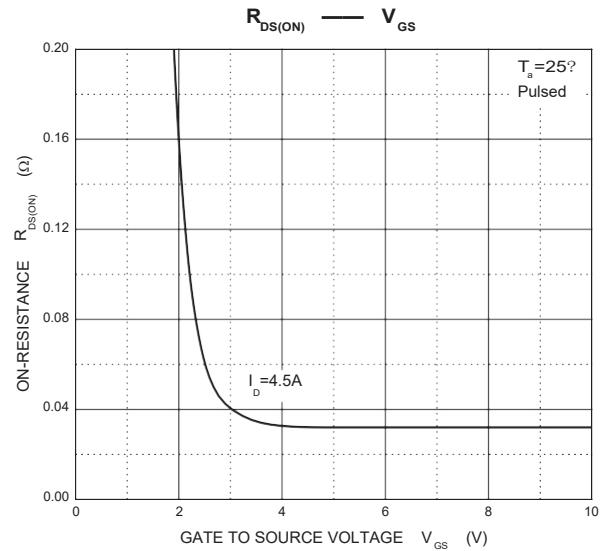
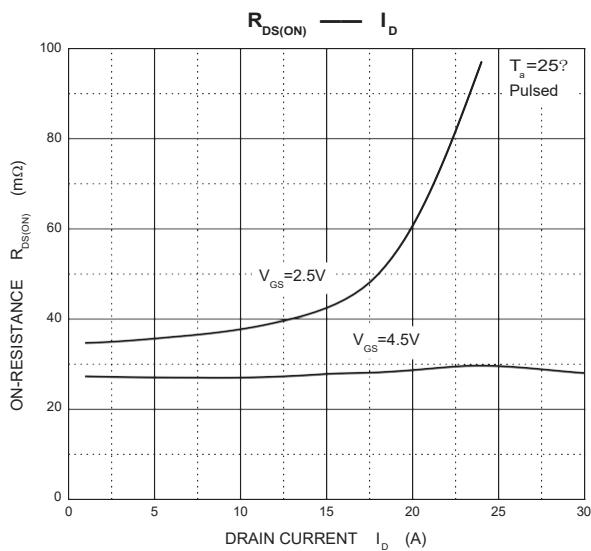
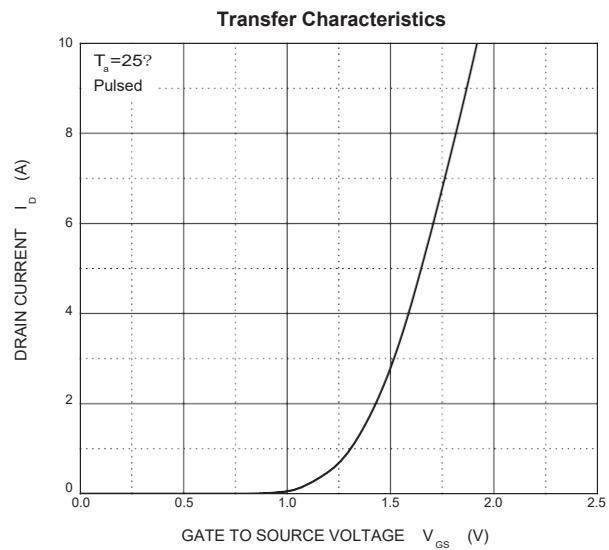
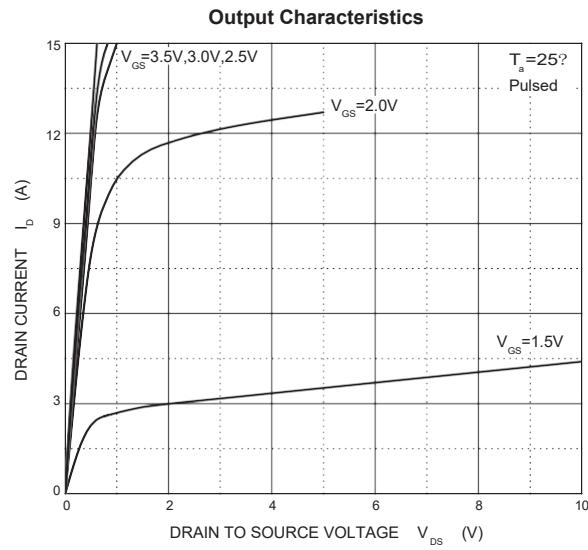
**Electrical characteristics ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 10\mu\text{A}$	20			V
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 50\mu\text{A}$	0.65	0.95	1.2	
Gate-body leakage	$I_{\text{GSS}}$	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 8\text{V}$			$\pm 100$	nA
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	$\mu\text{A}$
Drain-source on-resistance <sup>a</sup>	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 3.6\text{A}$		0.045	0.060	$\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 3.1\text{A}$		0.070	0.115	
Forward transconductance <sup>a</sup>	$g_{\text{fs}}$	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 3.6\text{A}$		8		S
Diode forward voltage	$V_{\text{SD}}$	$I_{\text{S}} = 0.94\text{A}, V_{\text{GS}} = 0\text{V}$		0.76	1.2	V
<b>Dynamic</b>						
Total gate charge	$Q_g$	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 3.6\text{A}$		4.0		nC
Gate-source charge	$Q_{\text{gs}}$			0.65		
Gate-drain charge	$Q_{\text{gd}}$			1.5		
Input capacitance <sup>b</sup>	$C_{\text{iss}}$	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		300		pF
Output capacitance <sup>b</sup>	$C_{\text{oss}}$			120		
Reverse transfer capacitance <sup>b</sup>	$C_{\text{rss}}$			80		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, R_L = 5.5\Omega, I_{\text{D}} \approx 3.6\text{A}, V_{\text{GEN}} = 4.5\text{V}, R_{\text{g}} = 6\Omega$		7	15	ns
Rise time	$t_r$			55	80	
Turn-off delay time	$t_{\text{d}(\text{off})}$			16	60	
Fall time	$t_f$			10	25	

**Notes :**

- a. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. These parameters have no way to verify.

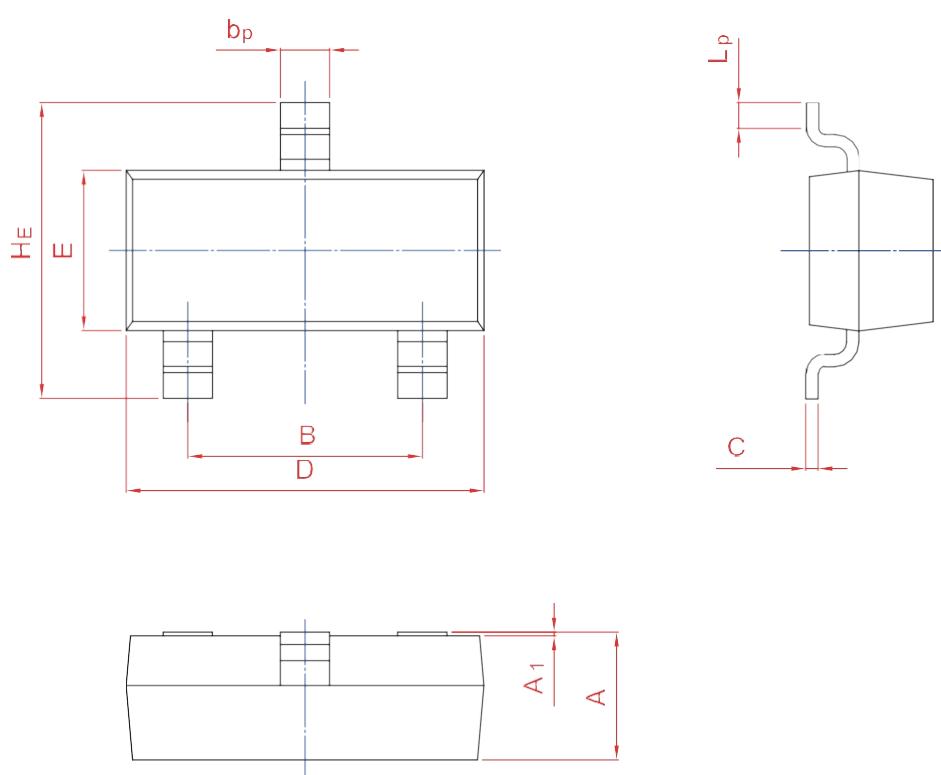
## Typical Characteristics



## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	$b_p$	C	D	$E$	$H_E$	$A_1$	$L_p$
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20